

ABSTRACT OF THE DISCLOSURE

A thin film transistor array panel is provided, which includes: a gate line formed on an insulating substrate; a gate insulating layer on the gate line; a semiconductor layer on the gate insulating layer; a data line formed on the gate insulating layer; a drain electrode formed at least
5 in part on the semiconductor layer; a first passivation layer formed on the data line and the drain electrode; a color filter formed on the data line and the drain electrode; a second passivation layer formed on the color filter; and a pixel electrode formed on the color filter, connected to the drain electrode, overlapping the second passivation layer, and enclosed by the second passivation layer.